

Application No.: 10/591,456

8 silicon nitride film  
9 silicon nitride film  
10 conductive film  
11 silicon substrate  
15 bonding wire  
21 substrate  
22 cavity  
23 insulating film  
24 air gap  
30 vibrating film

Please amend the paragraph beginning on page 5, line <sup>2</sup>13 as follows:

ycc  
2/24/10

[0019] Specifically, on a substrate 21 arranged on the resin substrate 1 and having a cavity 22, the vibrating electrode 5 is formed so as to cover the cavity 22. An electretized silicon [[oxide]] dioxide film 7 (a film that has become an electret by being charged) is formed on the vibrating electrode 5 with a silicon nitride film 9 interposed therebetween. The silicon [[oxide]] dioxide film 7 is arranged on the central part of the vibrating electrode 5. Further, a silicon nitride film 8 is formed so as to cover the silicon [[oxide]] dioxide film 7. Accordingly, the silicon [[oxide]] dioxide film 7 is completely covered with the silicon nitride film 8 and the silicon nitride film 9. In the present embodiment, the vibrating electrode 5, the silicon nitride film 9, the silicon [[oxide]] dioxide film 7, and the silicon nitride film 8 vibrate integrally to serve as a vibrating film 30.

Please amend the paragraph beginning on page 5, line <sup>12</sup>13 as follows:

ycc  
2/24/10

[0020] The fixed electrode 6 is formed above the vibrating film 30 with an insulating film 23 serving as a spacer interposed therebetween. In other words, the silicon [[oxide]] dioxide film 7 covered with the silicon nitride films 8 and 9 and an air gap 24 formed by partially removing the insulating film 23 intervene between the vibrating electrode 5 and the fixed

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electrode 6. In the fixed electrode 6, a plurality of acoustic holes 6a are formed so as to communicate with the air gap 24. Further, an opening 4a is formed at a part of the shielding case 4 facing the fixed electrode 6 so that the acoustic holes 6a receive sound pressure from the external space.

Please amend the paragraph beginning on page 5, line <sup>24</sup>~~25~~ as follows:

ycc  
2/24/10

[0022] As shown in FIG. 2(a), the vibrating film 30 may be formed in such a manner that the electrified silicon ~~[[oxide]]~~ dioxide film 7 is formed on the vibrating electrode 5 and the silicon nitride film 8 is formed so as to cover this silicon ~~[[oxide]]~~ dioxide film 7.

Please amend the paragraph beginning on page <sup>5</sup>6, line <sup>27</sup>~~1~~ as follows:

ycc  
2/24/10

[0023] Alternatively, as shown in FIG. 2(b), the vibrating film 30 may be formed in such a manner that the silicon nitride film 9 is formed on the vibrating electrode 5, the electrified silicon ~~[[oxide]]~~ dioxide film 7 is formed thereon, and then, the silicon nitride film 8 is formed so as to cover this silicon ~~[[oxide]]~~ dioxide film 7.

Please amend the paragraph beginning on page <sup>4f</sup>6, line <sup>4f</sup>~~5~~ as follows:

ycc  
2/24/10

[0024] In the vibrating film 30 shown in FIG. 2(a), the electret formed of the electrified silicon ~~[[oxide]]~~ dioxide film 7 is completely covered with the vibrating electrode 5 and the silicon nitride film 8. As to the vibrating film 30 shown in FIG. 2(b), the electret formed of the electrified silicon ~~[[oxide]]~~ dioxide film 7 is completely covered with the silicon nitride film 9 and the silicon nitride film 8. Either structures shown in FIG. 2(a) or FIG. 2(b) attain

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suppression of absorption of moisture in the air by the silicon [[oxide]] dioxide film 7 and of dissipation of charge from the silicon [[oxide]] dioxide film 7 at heating.

Please amend the paragraph beginning on page 6, line <sup>11</sup>~~12~~ as follows:

yes  
2/24/10

[0025] The present inventors carried out an experiment for verifying the effects obtained by completely covering the silicon [[oxide]] dioxide film 7 with the vibrating electrode 5 and the silicon nitride film 8 or with the silicon nitride film 9 and the silicon nitride film 8, as shown in FIG. 2(a) or FIG. 2(b). The results of the experiment will be described with reference to FIG. 3(a) and FIG. 3(b).

Please amend the paragraph beginning on page 6, line <sup>16</sup>~~17~~ as follows:

yes  
2/24/10

[0026] FIG. 3(a) is a section showing a structure of a film used in the verification of the effects obtained by completely covering the electrified silicon [[oxide]] dioxide film 7 with the silicon nitride films 8 and 9 in the electret condenser 2 of the present embodiment. FIG. 3(b) is a section showing a film structure where the electrified silicon [[oxide]] dioxide film 7 is exposed to an atmosphere, as a comparative example in the aforementioned verification. In each film structure in FIG. 3(a) or FIG. 3(b), the silicon [[oxide]] dioxide film 7 is formed on the obverse face of a silicon substrate 11, on the reverse face of which a conductive film (Al film) 10 is formed.

Please amend the paragraph beginning on page 6, line <sup>24</sup>~~25~~ as follows:

yes  
2/24/10

[0027] Specifically, the silicon [[oxide]] dioxide film 7 is an LP-TEOS (low pressure-tetraethylorthosilicate) film formed under reduced pressure to have a thickness of 1.5  $\mu\text{m}$ . It is

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noted that the temperature for forming the silicon [[oxide]] dioxide film 7 by, for example, reduced pressure CVD (Chemical Vapor Deposition) is preferably set in the range between 500 °C and 800 °C, both inclusive.

Please amend the paragraph beginning on page 7, line <sup>2</sup>3 as follows:

ycc  
2/24/10

[0028] Further, in the film structure shown in FIG. 3(a), the above-described silicon [[oxide]] dioxide film 7 is completely covered with the silicon nitride films 8 and 9, which are LP-SiN films formed under reduced pressure. Thus, with the use of the LP-SiN films formed by, for example, reduced pressure CVD at a high temperature as the silicon nitride films 8 and 9, the silicon nitride films 8 and 9 can serve as dense protection films with no pin hole and the like. Specifically, the temperature for growing the silicon nitride films 8 and 9 by, for example, reduced pressure CVD is preferably set in the range between 600 °C and 800 °C, both inclusive.

Please amend the paragraph beginning on page 7, line <sup>10</sup>11 as follows:

ycc  
2/24/10

[0029] The verification by the present inventors shows that in the film structure in which the silicon [[oxide]] dioxide film 7 to which charge is electro-deposited is exposed to the atmosphere (i.e., the film structure of the comparative example shown in FIG. 3(b)), a 44-hour shelf test reduced the amount of electrodeposition of the silicon [[oxide]] dioxide film 7 by approximately 8 dB. In contrast, in the film structure in which the silicon [[oxide]] dioxide film 7 to which charge is electro-deposited is completely covered with the silicon nitride film 8 and the silicon nitride film 9 (i.e., the film structure of the present embodiment ~~shown~~ shown in FIG. 3(a)), the reduced amount of electrodeposition of the silicon [[oxide]] dioxide film 7 was only approximately 0.4 dB after the 44-hour shelf test, for example. Further, even after the film

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structure of the present embodiment additionally underwent one-hour heating in an atmosphere at a temperature of 150 °C, the amount of electrodeposition of the silicon [[oxide]] dioxide film 7 was reduced by approximately 0.1 dB at utmost. In other words, with the film structure of the present embodiment, remarkable suppression can be observed in absorption of moisture and the like in the air by the silicon [[oxide]] dioxide film 7 and in charge dissipation from the silicon [[oxide]] dioxide film 7 at heating, compared with the film structure of the comparative example.

Please amend the paragraph beginning on page 7, line <sup>25</sup>~~27~~ as follows:

yec  
2/24/10

[0030] As described above, in the present embodiment, the electretized silicon [[oxide]] dioxide film 7 is covered with the silicon nitride films 8 and 9 or with the silicon nitride film 8 and the vibrating electrode 5, so that absorption of moisture and the like in the air by the silicon [[oxide]] dioxide film 7 and charge dissipation from the silicon [[oxide]] dioxide film 7 at heating can be suppressed. Hence, an electret condenser 2 excellent in reliability, such as moisture resistance and thermal resistance can be provided.

Please amend the paragraph beginning on page 8, line <sup>4</sup>~~6~~ as follows:

yec  
2/24/10

[0031] The principal of resonance frequency control for the vibrating film 30 will be described below by referring as an example to the case where the vibrating film 30 of the present embodiment is composed of the silicon [[oxide]] dioxide film 7 formed of a LP-TEOS film, the silicon nitride films 8 and 9 formed of LP-SiN films, and the vibrating electrode 5 formed of a polysilicon film (a so-called polysilicon-doped film) to which an impurity is doped (see FIG.2(b)).

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Please amend the paragraph beginning on page 9, line <sup>8</sup>10 as follows:

ycc  
2/24/10

[0035] For example, on the assumption that: an area of the quadratic film to be the vibrating film 30 is  $1 \text{ mm}^2$  ( $a = 1 \text{ mm}$ ); the film thickness  $d1$  of the LP-TEOS film to be the silicon [[oxide]] dioxide film 7 (stress ( $\sigma1$  in (Expression 7)):  $-110 \times 10^6 \text{ [N/m}^2\text{]}$  and density ( $\rho1$  in (Expression 8)):  $2.5 \times 10^3 \text{ [kg/m}^3\text{]}$ ) is  $1500 \text{ nm}$ ; each film thickness  $d2$  of the LP-SiN films to be the silicon nitride films 8 and 9 (stress ( $\sigma2$  in (Expression 7)):  $1200 \times 10^6 \text{ [N/m}^2\text{]}$  and density ( $\rho2$  in (Expression 8)):  $3.1 \times 10^3 \text{ [kg/m}^3\text{]}$ ); and a film thickness  $d3$  of the polysilicon film to be the vibrating electrode 5 (stress ( $\sigma3$  in (Expression 7)):  $-0.3 \text{ [N/m}^2\text{]}$  and density ( $\rho3$  in (Expression 8)):  $2.3 \times 10^3 \text{ [kg/m}^3\text{]}$ ) is  $200 \text{ nm}$ , the resonance frequency  $f$  is calculated to be  $178 \text{ kHz}$  from (Expression 1) through (Expression 8). Accordingly, when the LP-TEOS film and the LP-SiN films are changed in thickness on the basis of this value as a standard resonance frequency  $f0$ , the resonance frequency  $f$  can be controlled.

Please amend the paragraph beginning on page 9, line <sup>19</sup>22 as follows:

ycc  
2/24/10

[0036] As shown in FIG. 1, the electret condenser 2 of the present embodiment serves as a component part of the microphone. The microphone changes sound pressure to an electric signal signal in the frequency band of 2 to 20 kHz, which is the audible region. Accordingly, the vibrating film 30 of the electret condenser 2 must have a resonance frequency  $f$  higher than 20 kHz, the upper limit of the frequency band. Otherwise, it exhibits insufficient sensitivity to be of no use as a component part of the microphone. In the present embodiment, as described above, when each film thickness of the silicon [[oxide]] dioxide film 7 and the silicon nitride films 8 and 9, which compose the vibrating film 30, is adjusted, the vibrating film 30 having a resonance frequency  $f$  over 20 kHz can be formed.

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Please amend the paragraph beginning on page 10, line <sup>4</sup>8 as follows:

ycc  
2/24/10

[0038] As described above, according to the present embodiment, control of each film thickness of the multilayer film (the silicon [[oxide]] dioxide film 7, the silicon nitride films 8 and 9, and the like) composing the vibrating film 30 leads to control of the resonance frequency f of the vibrating film 30.

Please amend the paragraph beginning on page 10, line <sup>8</sup>12 as follows:

ycc  
2/24/10

[0039] It should be noted that it is preferable that the silicon [[oxide]] dioxide film 7 is set smaller in shape in plan than, for example, the quadratic film to be the vibrating film 30 and is arranged at the central part of the vibrating film 30. This allows the silicon [[oxide]] dioxide film 7 which is to be an electret to be used as a mass (a weight) in the vibrating film 30, enhancing the sensitivity of the electret condenser 2 of the present embodiment. Further, the film thickness of the multilayer film composing the vibrating film 30 can be reduced in a region where the silicon [[oxide]] dioxide film 7 is not formed.

Please amend the paragraph beginning on page 10, line <sup>15</sup>19 as follows:

ycc  
2/24/10

[0040] Moreover, in the present embodiment, the silicon [[oxide]] dioxide film 7 is used as an electret, but the electret may be another insulating film made of polytetrafluoroethylene, FEP, or the like.

Please amend the paragraph beginning on page 10, line <sup>18</sup>22 as follows:

ycc  
2/24/10

[0041] In addition, the silicon nitride films 8 and 9 are used as the insulating films for covering the electret formed of the silicon [[oxide]] dioxide film 7 in the present embodiment, but other insulating films made of polyimide, benzocyclobutene, or the like may be used instead.